

# Cascadable Silicon Bipolar MMIC Amplifier

# Technical Data

#### **MSA-0505**

#### **Features**

- Cascadable 50  $\Omega$  Gain Block
- High Output Power:  $18.0~\mathrm{dBm}$  Typical  $\mathrm{P_{1~dB}}$  at  $1.0~\mathrm{GHz}$
- Low Distortion: 29.0 dBm Typical IP<sub>3</sub> at 1.0 GHz
- 7.0 dB Typical Gain at 1.0 GHz
- Surface Mount Plastic Package
- Tape-and-Reel Packaging Option Available<sup>[1]</sup>

#### Note:

1. Refer to PACKAGING section "Tape-and-Reel Packaging for Semiconductor Devices."

## **Description**

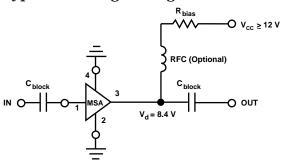
The MSA-0505 is a high performance medium power silicon bipolar Monolithic Microwave Integrated Circuit (MMIC) housed in a low cost, surface mount package. This MMIC is designed for use as a general purpose 50  $\Omega$  gain block. Typical applications include narrow and broad band IF and RF amplifiers in commercial systems.

The MSA-series is fabricated using HP's  $10\,\mathrm{GHz}\,\mathrm{f_T}, 25\,\mathrm{GHz}\,\mathrm{f_{MAX}},$  silicon bipolar MMIC process which uses nitride self-alignment, ion implantation, and gold metallization to achieve excellent performance, uniformity and reliability. The use of an external bias resistor for temperature and current stability also allows bias flexibility.

## 05 Plastic Package



## **Typical Biasing Configuration**



5965-9581E 6-354

## **MSA-0505 Absolute Maximum Ratings**

Parameter	Absolute Maximum <sup>[1]</sup>
Device Current	135 mA
Power Dissipation <sup>[2,3]</sup>	1.5W
RF Input Power	+25 dBm
Junction Temperature	200℃
Storage Temperature	−65 to 150°C

Thermal Resistance $^{[2,4]}$ :	
$\theta_{\rm jc} = 85^{\circ} \text{C/W}$	

#### **Notes:**

- 1. Permanent damage may occur if any of these limits are exceeded.
- 2.  $T_{CASE} = 25$ °C.
- 3. Derate at 11.8 mW/°C for  $T_C > 73$ °C.
- 4. See MEASUREMENTS section "Thermal Resistance" for more information.

# Electrical Specifications<sup>[1]</sup>, $T_A = 25$ °C

Symbol	Parameters and Test Conditions:	Units	Min.	Тур.	Max.	
P <sub>1 dB</sub>	Output Power at 1 dB Gain Compression	f = 0.5 GHz f = 1.0 GHz	dBm dBm	16.0	19.0 18.0	
GP	PowerGain( $ S_{21} ^2$ )	f = 0.5 GHz f = 1.0 GHz	dB	6.0	7.5 7.0	
$\Delta G_{ m P}$	Gain Flatness	f = 0.1  to  1.5  GHz	dB		± 0.75	
f <sub>3 dB</sub>	3 dB Bandwidth <sup>[2]</sup>		GHz		2.3	
MOMAD	Input VSWR	f = 0.1 to 1.5 GHz			1.6:1	
VSWR	Output VSWR	f = 0.1  to  1.5  GHz			2.0:1	
$IP_3$	Third Order Intercept Point	f = 1.0  GHz	dBm		29.0	
NF	$50\Omega$ Noise Figure	f = 1.0  GHz	dB		6.5	
$t_{\mathrm{D}}$	Group Delay	f = 1.0 GHz	psec		190	
V <sub>d</sub>	Device Voltage		V	6.7	8.4	10.1
dV/dT	Device Voltage Temperature Coefficient		mV/°C		-16.0	

#### Notes

- 1. The recommended operating current range for this device is 60 to 100 mA. Typical performance as a function of current is on the following page.
- 2. Referenced from  $0.1 \text{ GHz Gain } (G_P)$ .

## **Part Number Ordering Information**

Part Number	No. of Devices	Container		
MSA-0505-TR1	500	7" Reel		
MSA-0505-STR	10	Strip		

For more information, see "Tape and Reel Packaging for Semiconductor Devices".

MSA-0505 Typical Scattering Parameters ( $T_A = 25^{\circ}C$ ,  $I_d = 80$  mA)

Freq.	$S_1$	1		$\mathbf{S_{21}}$		$\mathbf{S_{12}}$					
MHz	Mag	Ang	dB	Mag	Ang	dB	Mag	Ang	Mag	Ang	k
5	.56	<b>-</b> 39	14.9	5.56	161	-18.5	.120	39	.65	-36	0.60
25	.24	<b>-</b> 103	9.7	3.05	156	-13.9	.202	12	.25	<b>-</b> 90	0.97
50	.15	-130	8.2	2.57	163	-13.7	.207	7	.15	-116	1.15
100	.13	<b>-</b> 155	7.8	2.45	165	-13.7	.207	3	.11	<b>-</b> 132	1.21
200	.12	-170	7.7	3.43	161	-13.5	.211	1	.11	<b>-</b> 145	1.21
400	.12	178	7.5	2.37	148	-13.6	.209	<b>-</b> 1	.14	<b>-</b> 146	1.23
600	.13	172	7.4	2.34	134	-13.6	.209	<b>-</b> 2	.17	-151	1.23
800	.13	168	7.2	2.29	119	-13.6	.209	<b>-</b> 3	.21	-157	1.23
1000	.14	166	7.0	2.24	105	-13.4	.213	<del>-4</del>	.25	-164	1.21
1500	.21	159	6.4	2.09	72	-13.3	.217	<b>-</b> 6	.34	176	1.16
2000	.30	148	5.2	1.82	42	-13.1	.222	<b>-</b> 9	.42	159	1.12
2500	.40	136	4.1	1.60	17	-12.9	.227	-11	.48	146	1.05
3000	.52	121	2.7	1.36	<b>-</b> 7	-12.6	.234	-16	.55	133	0.92

A model for this device is available in the DEVICE MODELS section.

# Typical Performance, $T_A = 25^{\circ}C$

(unless otherwise noted)

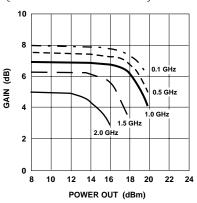


Figure 1. Typical Gain vs. Power Out,  $T_A = 25^{\circ}C$ ,  $I_d = 80$  mA.

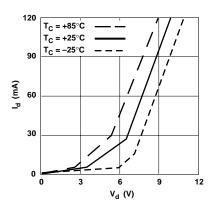


Figure 2. Device Current vs. Voltage.

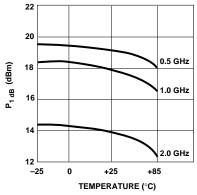


Figure 3. Output Power at 1 dB Gain Compression, vs. Case Temperature,  $I_d = 80\ mA.$ 

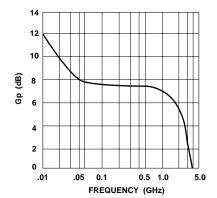


Figure 4. Gain vs. Frequency,  $I_d$  = 80 to 100 mA.

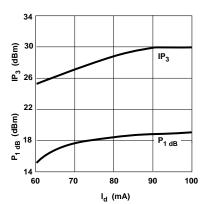
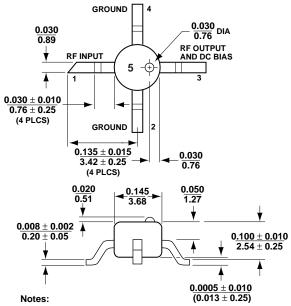


Figure 5. Output Power at 1 dB Gain Compression, Third Order Intercept vs. Case Temperature, f = 1.0 GHz.

## **05 Plastic Package Dimensions**



(unless otherwise specified)

1. Dimensions are in mm

- 2. Tolerances

in .xxx =  $\pm 0.005$ mm .xx =  $\pm$  0.13